Product data sheet

1. General description

High voltage, high speed, planar passivated NPN power switching transistor in a TO92 plastic package.

2. Features and benefits

- Fast switching
- High voltage capability
- · Very low switching and conduction losses

3. Applications

- · Compact fluorescent lamps (CFL)
- Electronic lighting ballasts
- Inverters
- · Off-line self-oscillating power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions Values			Unit			
Absolute	Absolute maximum rating							
V _{CESM}	collector-emitter peak voltage V _{BE} = 0 V 700				V			
I _C	collector current	DC; <u>Fig. 1</u>	1			Α		
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 2</u>	2.1			W		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static ch	Static characteristics							
h _{FE}	DC current gain	I _C = 0.8 A; V _{CE} = 5 V; T _{lead} = 25 °C; Fig. 8; Fig. 9		5	7.5	20		

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C
2	С	collector]	
3	Е	emitter		B—L
			$\widetilde{\mathbb{I}}$	I E
			3 2 1 TO-92 (SOT54)	sym131

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
PHE13003A	TO92	PHE13003A,412	Bulk	1000	SOT54	14-Nov-2013
PHE13003A	TO92	PHE13003A,126	Reel	2000	SOT54 wide pitch	14-Nov-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes
PHE13003A	13003A

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	700	V
V _{CBO}	collector-base voltage	I _E = 0 A	-	700	V
V _{CEO}	collector-emitter voltage	I _B = 0 A	-	400	V
V _{EBO}	emitter-base voltage	I _C = 0 A; I(Emitter) = 10 mA	-	9	V
I _C	collector current	DC; Fig. 1	-	1	А
I _{CM}	peak collector current		-	3	Α
I _B	base current	DC	-	0.75	Α
I _{BM}	peak base current		-	1.5	Α
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 2</u>	-	2.1	W
T _{stg}	storage temperature		-65	150	°C
T _j	junction temperature		-	150	°C

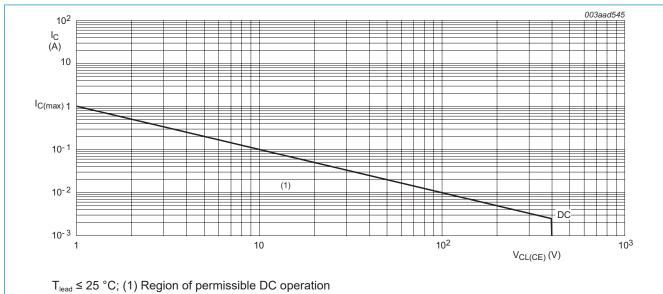
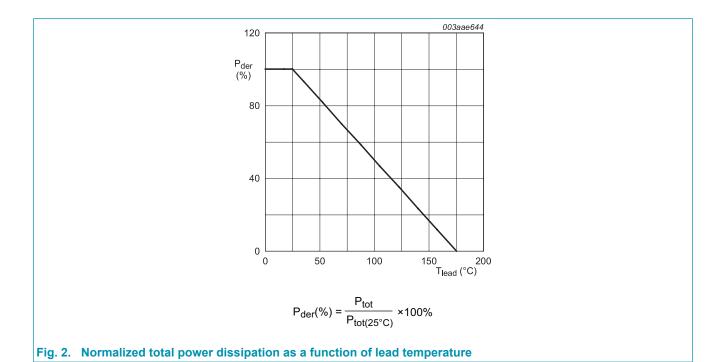


Fig. 1. Forward bias safe operating area

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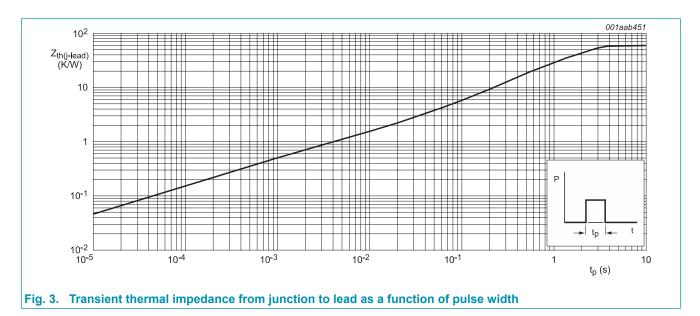


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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	Fig. 3	-	-	60	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air; printed-circuit board mounted; lead length = 4 mm	-	150	-	K/W



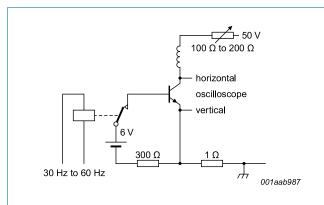
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics		,			_
I _{CES}	collector-emitter cut-off current (base shorted)	V _{BE} = 0 V; V _{CE} = 700 V; T _j =125°C	-	-	5	mA
I _{EBO}	emitter-base cut-off current (collector open)	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{lead} = 25^{\circ}\text{C}$	-	-	1	mA
V _{CEOsus}	collector-emitter sustaining voltage (base open)	$I_B = 0 \text{ A}; I_C = 1 \text{ mA}; L_C = 25 \text{ mH};$ $T_{lead} = 25^{\circ}\text{C}; \underline{\text{Fig. 4}}; \underline{\text{Fig. 5}}$	400	-	-	V
V _{CEsat}	collector-emitter saturation voltage	I _C = 0.25 A; I _B = 50 mA; T _{lead} = 25°C; Fig. 6	-	0.2	0.5	V
		I_{C} = 0.5 A; I_{B} = 125 mA; T_{lead} = 25°C; Fig. 6	-	09.3	1	V
		I_{C} = 0.75 A; I_{B} = 250 mA; T_{lead} = 25°C; Fig. 6	-	0.4	1.5	V
V _{BEsat}	base-emitter saturation voltage	$I_{\rm C}$ = 0.25 A; $I_{\rm B}$ = 50 mA; $T_{\rm lead}$ = 25°C; <u>Fig. 7</u>	-	-	1	V
		I_{C} = 0.5 A; I_{B} = 125 mA; T_{lead} = 25°C; Fig. 7	-	-	1.2	V
h _{FE}	DC current gain	$I_{\rm C}$ = 0.5 mA; $V_{\rm CE}$ = 2 V; $T_{\rm j}$ = 25°C; Fig. 8; Fig. 9	12	-	-	
		$I_{C} = 0.4 \text{ A}$; $V_{CE} = 5 \text{ V}$; $T_{j} = 25^{\circ}\text{C}$; Fig. 8; Fig. 9	10	-	30	
		$I_{c} = 0.8 \text{ A}$; $V_{ce} = 5 \text{ V}$; $T_{j} = 25^{\circ}\text{C}$; Fig. 8; Fig. 9	5	7.5	20	
Dynamic	characteristics	·				
t _f	fall time	I_{C} = 1 A; I_{Bon} = 200 mA; V_{BB} = -5 V; L_{B} = 1 μ H; T_{lead} = 25 °C; inductive load; <u>Fig. 10</u> ; <u>Fig. 11</u>	-	80	-	ns

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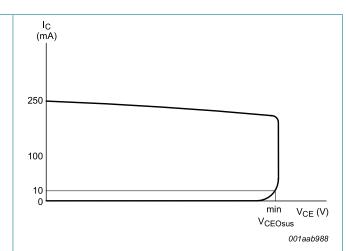
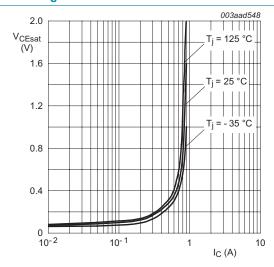
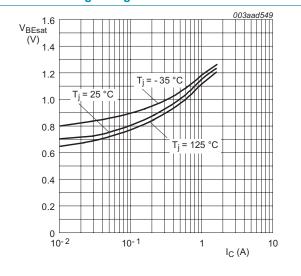


Fig. 4. Test circuit for collector-emitter sustaining voltage

Fig. 5. Oscilloscope display for collector-emitter sustaining voltage test waveform

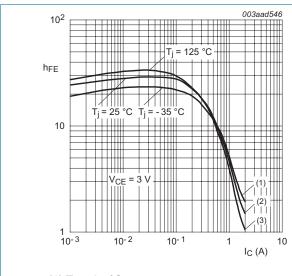




I_C / I_B = 5
 Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values

I_C / I_B = 5
 Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

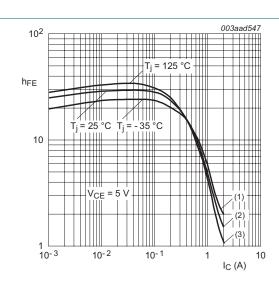
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(1) $T_j = -35 \,^{\circ}C$ (2) $T_j = 25 \,^{\circ}C$

(3) $T_j = 125 \,^{\circ}\text{C}$

Fig. 8. DC current gain as a function of collector current; typical values

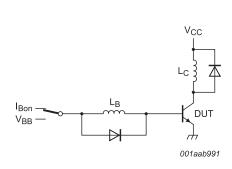


(1) $T_j = -35 \, ^{\circ}C$

(2) $T_j = 25 \,^{\circ}\text{C}$

(3) $T_j = 125 \, ^{\circ}C$

Fig. 9. DC current gain as a function of collector current; typical values



 $V_{CC}=300~V;~V_{BB}=-5~V;~L_{C}=200~\mu H;~L_{B}=1~\mu H.$ Fig. 7. Test circuit for inductive load switching

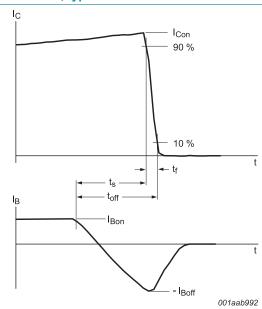
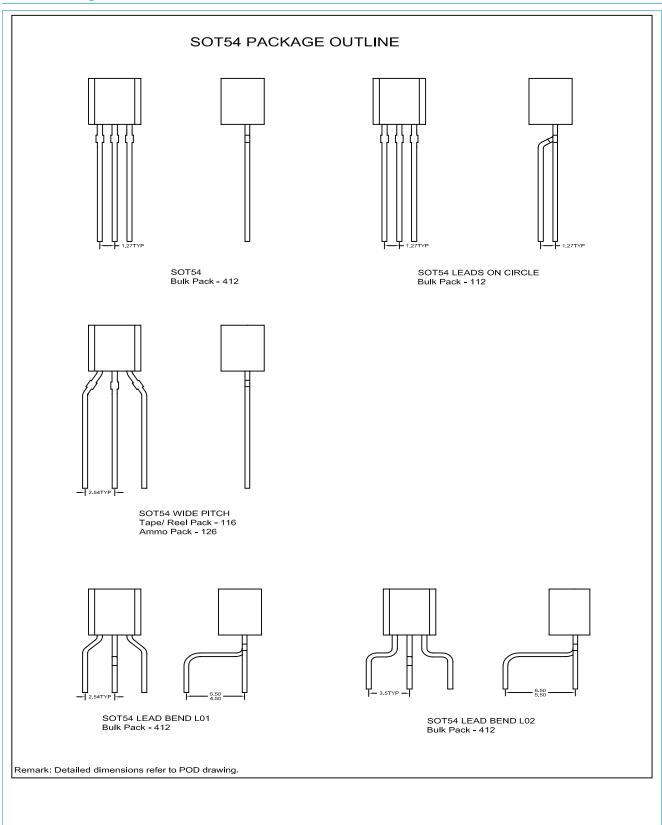
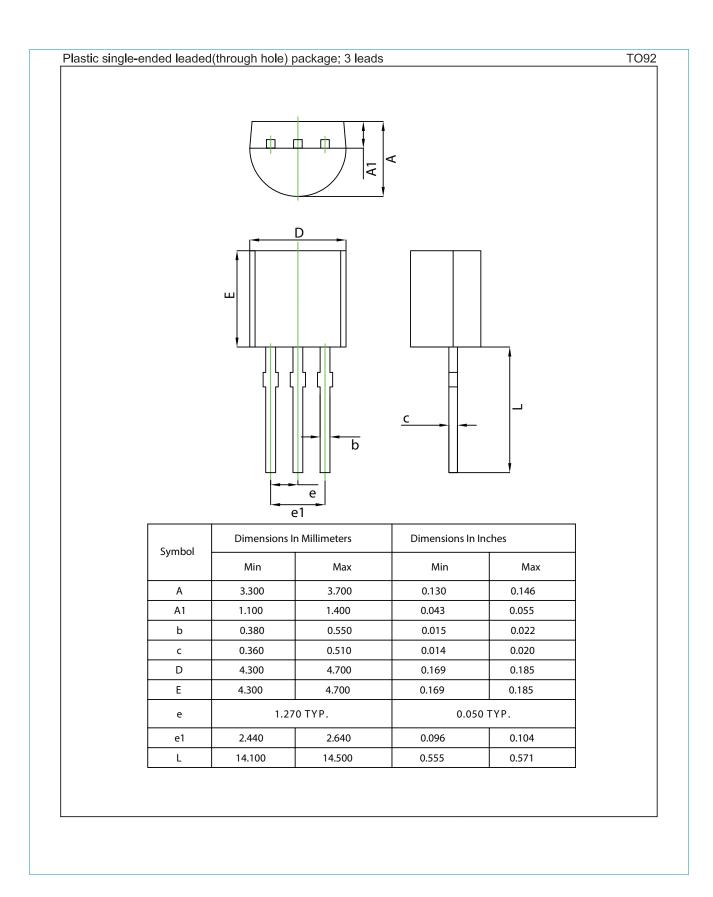


Fig. 8. Switching times waveforms for inductive load

11. Package outline





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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Date of release: 10 October 2021

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